

4A, 600V Ultrafast Diodes

The RURD460, and RURD460S are ultrafast diodes with soft recovery characteristics ($t_{rr} < 55\text{ns}$). They have low forward voltage drop and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Formerly developmental type TA49035.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RURD460	TO-251	RUR460
RURD460S	TO-252	RUR460

NOTE: When ordering, use the entire part number. Add suffix 9A to obtain the TO-252 variant in tape and reel, i.e., RURD460S9A.

Symbol



Features

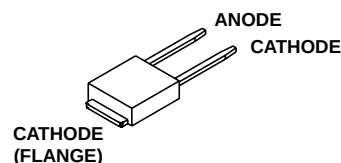
- Ultrafast with Soft Recovery <55ns
- Operating Temperature. 175°C
- Reverse Voltage 600V
- Avalanche Energy Rated
- Planar Construction

Applications

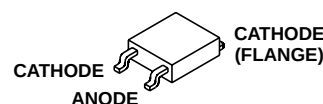
- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Packaging

JEDEC STYLE TO-251



JEDEC STYLE TO-252



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

	RURD460 RURD460S	UNITS
Peak Repetitive Reverse Voltage V_{RRM}	600	V
Working Peak Reverse Voltage V_{RWM}	600	V
DC Blocking Voltage V_R	600	V
Average Rectified Forward Current $I_F(AV)$ ($T_C = 160^\circ\text{C}$)	4	A
Repetitive Peak Surge Current I_{FRM} (Square Wave, 20kHz)	8	A
Nonrepetitive Peak Surge Current I_{FSM} (Halfwave, 1 phase, 60Hz)	40	A
Maximum Power Dissipation P_D	50	W
Avalanche Energy (See Figures 9 and 10) E_{AVL}	10	mJ
Operating and Storage Temperature T_{STG}, T_J	-65 to 175	°C
Maximum Lead Temperature for Soldering		
Leads at 0.063 in. (1.6mm) from case for 10s T_L	300	°C
Package Body for 10s, see Tech Brief 334. T_{PKG}	260	°C

Electrical Specifications $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNITS
V_F	$I_F = 4\text{A}$	-	-	1.5	V
	$I_F = 4\text{A}, T_C = 150^\circ\text{C}$	-	-	1.2	V
I_R	$V_R = 600\text{V}$	-	-	100	μA
	$V_R = 600\text{V}, T_C = 150^\circ\text{C}$	-	-	500	μA
t_{rr}	$I_F = 1\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	55	ns
	$I_F = 4\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	60	ns
t_a	$I_F = 4\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	32	-	ns
t_b	$I_F = 4\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	15	-	ns
Q_{RR}	$I_F = 4\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	50	-	nC
C_J	$V_R = 10\text{V}, I_F = 0\text{A}$	-	15	-	pF
$R_{\theta JC}$		-	-	3	$^\circ\text{C}/\text{W}$

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300 μs , D = 2%).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time (See Figure 8), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current (See Figure 8).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 8).

Q_{RR} = Reverse recovery time.

C_J = Junction capacitance.

$R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

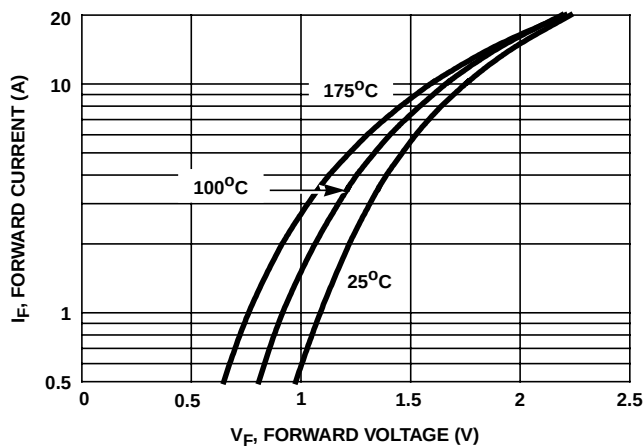


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

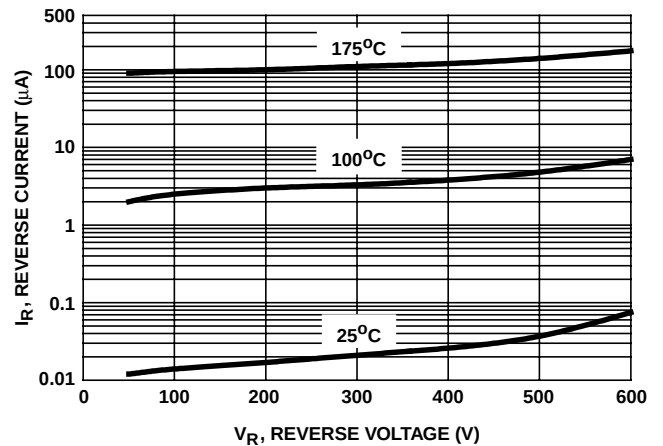


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE